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	APPLICANT  TSUCHIYA et al.	
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## U.S. Patent Documents

### Foreign Patent Documents

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

<i>M. B.</i>	R. Bhat et al, "High-Performance 1.3 $\mu$ m AlGaNAs/InP Strained Quantum Well Lasers Grown by Organometallic Chemical Vapor Deposition", Journal of Crystal Growth (1004), pp: 858-865
	P.J.A. Thijs et al., "High Performance Buried Heterostructure $\lambda$ =1.5 $\mu$ m InGaAs/AlGaNAs Strained-Layer Quantum Well Laser Diodes", 10 <sup>th</sup> International Conference on Indium Phosphide and Related Materials (1996) ThA2-2, pp. 765-768
	Tawee Tanbun-Ek et al., "High Performance Buried Heterostructure 1.55 $\mu$ m Wavelength AlGaNAs/InP Multiple Quantum Well Lasers Grown Entirely by NOVPE Technique", 10 <sup>th</sup> International Conference on Indium Phosphide and Related Materials (May 1998) ThP-48, pp. 702-705
<i>C. E.</i>	C. E. Zah et al., "High-Temperature Modulation Dynamics of 1.3 $\mu$ m Al <sub>x</sub> Ga <sub>y</sub> In <sub>1-x-y</sub> As/InP Compressive-Strained Multiple-Quantum-Well Lasers", 14 <sup>th</sup> International Semiconductor Laser Conference (1994), TH 1.3, pp. 215-216
EXAMINER	<i>John M. Sauer</i>
	DATE CONSIDERED
	<i>7/26/05</i>

**EXAMINER:** Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant